

WHAT IS CLAIMED IS:

1. A method for forming a pattern over a substrate,
comprising:

providing a substrate having an etching layer formed
thereon;

locating a master having at least one opening in the etching
layer;

filling a resist in the at least one opening of the master;
and

separating the master from the substrate to leave the resist
on the substrate.
2. The method of claim 1, wherein the filling a resist in
the at least one opening of the master comprises:

contacting a resist supplying roll to the master; and

filling the resist in the at least one opening of the master
by rotating the resist supplying roll over the at least one
opening of the master.

3. The method of claim 1, wherein the filling a resist in the at least one opening of the master comprises:

applying the resist on the master; and

planarizing the applied resist on the surface of the master by using a doctor blade.

4. The method of claim 1, wherein the master is separated apart from the substrate by a few micrometers (μm).

5. The method of claim 1, wherein the etching layer is a metal layer.

6. The method of claim 1, wherein the etching layer is an insulating layer.

7. The method of claim 6, wherein the insulating layer is formed of one of SiO_x or SiN_x .

8. The method of claim 1, wherein the etching layer is a semiconductor layer.

9. The method of claim 1, further comprising hardening the resist.

10. A method for forming a pattern over a substrate, comprising:

providing a substrate having an etching layer formed thereon;

placing a master having at least one opening on an area corresponding to the etching layer to be etched;

applying a resist on the master;

planarizing the applied resist on the surface of the master and filling the resist in the at least one opening by using a doctor blade;

hardening the planarized resist; and

forming a resist pattern on the etching layer by separating the master from the substrate.

11. The method of claim 10, wherein the master is separated apart from the substrate by a few micrometers (μm).

12. A method for forming a pattern over a substrate, comprising:

providing a substrate having an etching layer formed thereon;

placing a master having at least one opening corresponding to the etching layer to be etched;

contacting a resist supplying roll on the master to fill the resist in the at least one opening of the master;

hardening the filled resist in the at least one opening of the master; and

forming a resist pattern on the etching layer by separating the master from the substrate.

13. The method of claim 12, wherein the master is separated apart from the substrate by a few micrometers (μm).